## NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

## Absolute Maximum Ratings (T<sub>a</sub> = 25<sup>o</sup>C)

	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	V <sub>CBO</sub> 35	
Collector Emitter Voltage	V <sub>CEO</sub>	30	V
Emitter Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	Ι <sub>c</sub>	800	mA
Base Current	Ι <sub>Β</sub>	160	mA
Power Dissipation	P <sub>tot</sub>	600	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







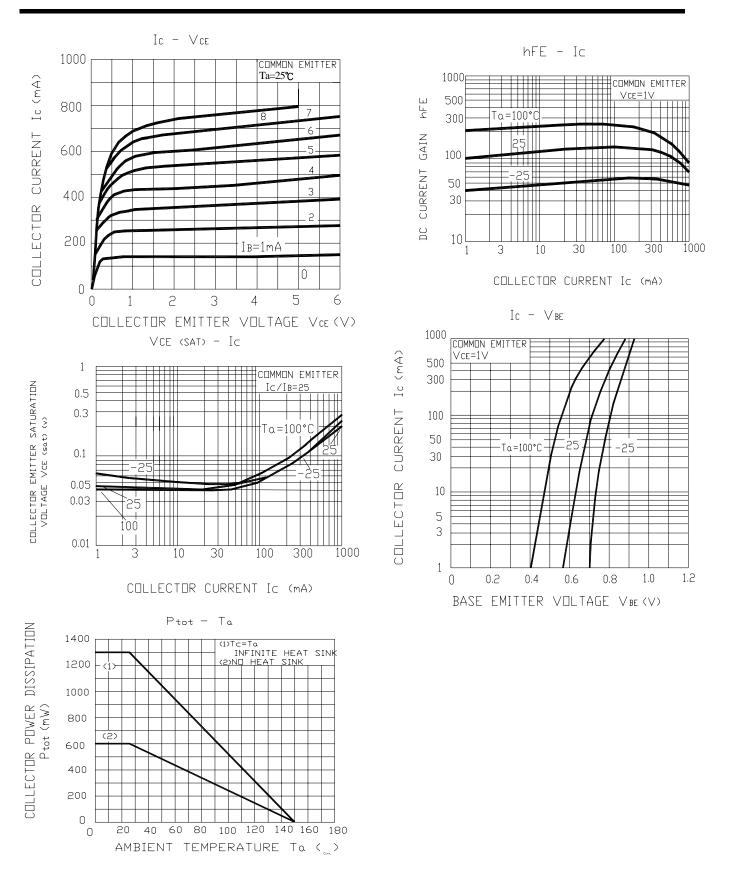
## Characteristics at $T_{amb}=25$ °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V <sub>CE</sub> =1V, I <sub>C</sub> =100mA					
Current Gain Group O	$h_{FE}$	100	-	200	-
Y	$h_{FE}$	160	-	320	-
at V <sub>CE</sub> =1V, I <sub>C</sub> =700mA	h <sub>FE</sub>	35	-	-	-
Collector Cutoff Current					
at V <sub>CB</sub> =35V	I <sub>CBO</sub>	-	-	0.1	μA
Emitter Cutoff Current					
at V <sub>EB</sub> =5V	I <sub>EBO</sub>	-	-	0.1	μΑ
Collector Emitter Saturation Voltage					
at I <sub>C</sub> =500mA, I <sub>B</sub> =20mA	$V_{\text{CE(sat)}}$	-	-	0.5	V
Transition Frequency					
at V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	f⊤	-	120	-	MHz
Base Emitter Voltage					
at $I_C=10mA$ , $V_{CE}=1V$	$V_{BE}$	0.5	-	0.8	V
Collector Output Capacitance					
at V <sub>CB</sub> =10V, f=1MHz	C <sub>OB</sub>	-	13	-	pF
Collector Emitter Breakdown Voltage					
at I <sub>c</sub> =10mA	$V_{CEO}$	30	-	-	V















Dated : 07/12/2002